



20V N-Channel Mosfet

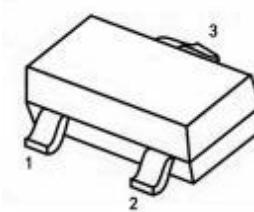
FEATURES

- $R_{DS(ON)} \leq 24m\Omega$ (21.6m Ω Typ.) @ $V_{GS}=4.5V$
- $R_{DS(ON)} \leq 37m\Omega$ (27m Ω Typ.) @ $V_{GS}=2.5V$

APPLICATIONS

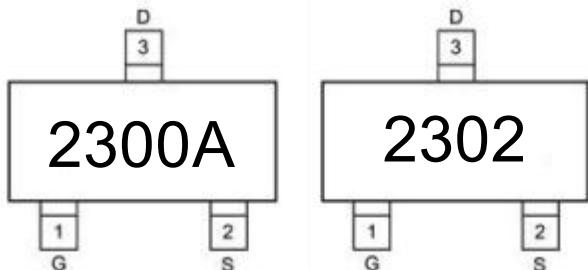
- PWM Applications
- Load Switch
- Power Management

SOT-23



1. GATE
2. SOURCE
3. DRAIN

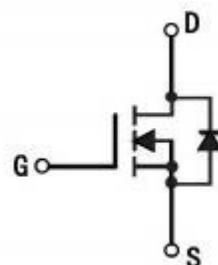
MARKING



2300A : Device code

2302: Device code

N-CHANNEL MOSFET

MAXIMUM RATINGS ($T_a=25^\circ C$ unless otherwise noted)

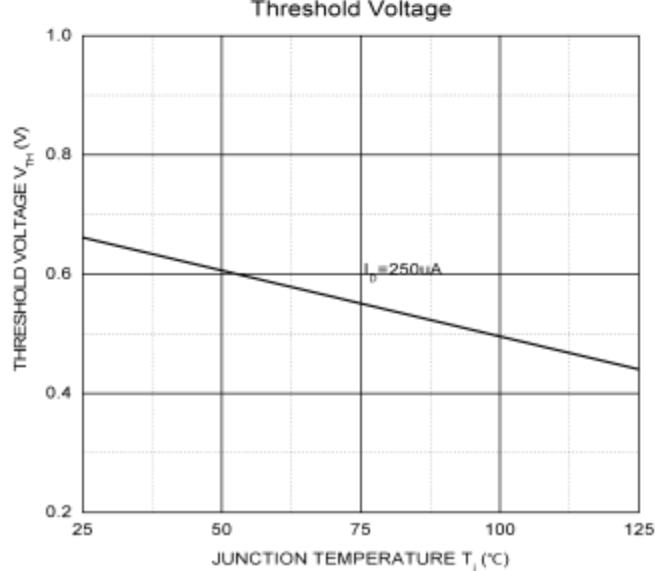
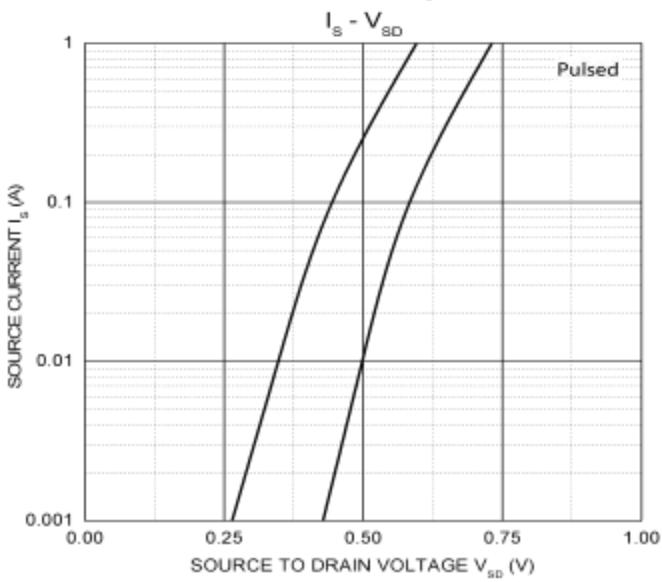
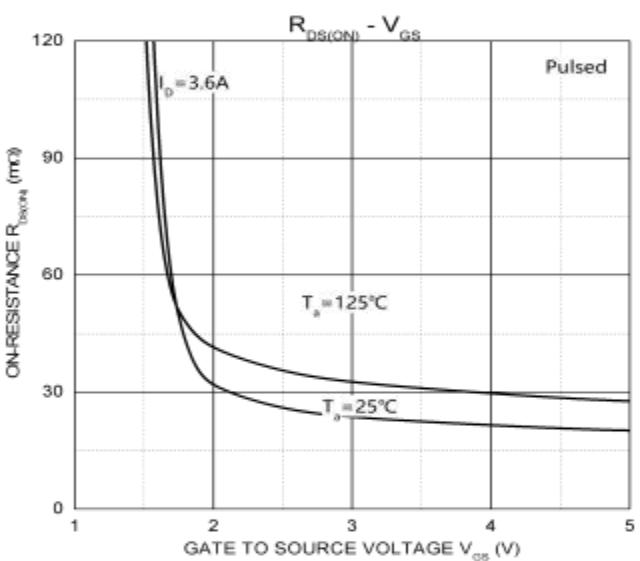
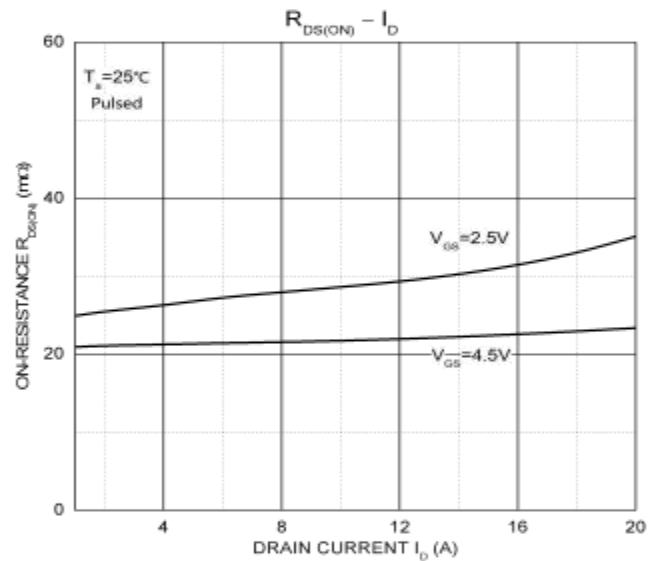
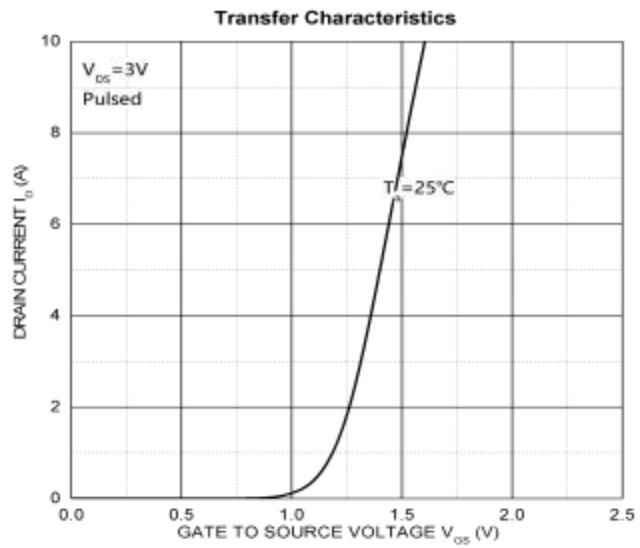
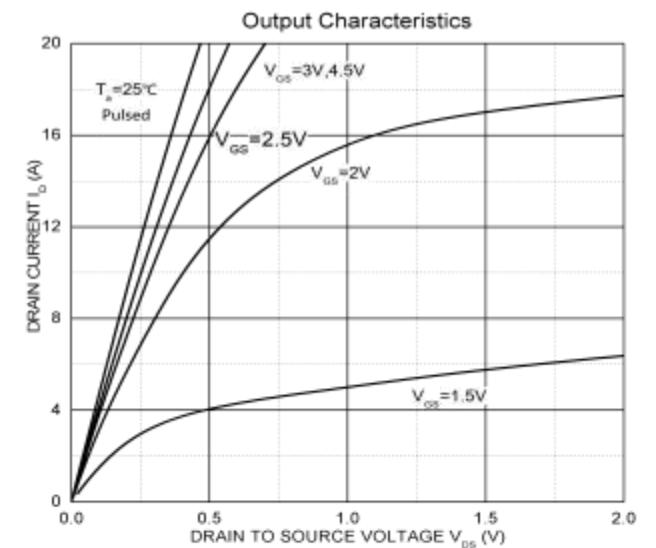
Symbol	Parameter	Value	Unit
V_{DS}	Drain- Source Voltage	20	V
V_{GS}	Gate- Source Voltage	± 12	V
I_D	Continuous Drain Current	5	A
I_{DM}	Plused Drain Current	25	A
P_D	Power Dissipation	0.35	W
$R_{\theta JA}$	Thermal Resistance from Junction to Ambient	357	C/ W
T_J	Junction Temperature	150	C
T_{STG}	Storage Temperature	-55~ +150	C



MOSFET ELECTRICAL CHARACTERISTICS Ta=25 °C unless otherwise specified

Symbol	Parameter	Test Condition	Min.	Typ.	Max.	Units
Off Characteristic						
V _{(BR)DSS}	Drain-Source Breakdown Voltage	V _{GS} = 0V, I _D = 250 μA	20	-	-	V
I _{DSS}	Zero Gate Voltage Drain Current	V _{DS} = 20V, V _{GS} = 0V, T _J = 25°C	-	-	1	μA
I _{GSS}	Gate to Body Leakage Current	V _{GS} = ± 12V, V _{DS} = 0V	-	-	±100	nA
On Characteristics						
V _{GS(th)}	Gate Threshold Voltage	V _{DS} =V _{GS} , I _D = 250 μA	0.5	0.66	1.2	V
R _{D(on)}	Static Drain-Source On-Resistance	V _{GS} = 4.5V, I _D = 4A	-	21.6	24	mΩ
		V _{GS} = 2.5V, I _D = 3A	-	27	37	
Dynamic Characteristics						
C _{iss}	Input Capacitance	V _{DS} = 10V, V _{GS} = 0V, f = 1.0MHz	-	800	-	pF
C _{oss}	Output Capacitance		-	155	-	pF
C _{rss}	Reverse Transfer Capacitance			125	-	pF
Q _g	Total Gate Charge	V _{DS} = 10V, I _D = 4A, V _{GS} = 4.5V,	-	11	-	nC
Q _{gs}	Gate-Source Charge		-	2.3	-	nC
Q _{gd}	Gate-Drain("Miller") Charge		-	2.5	-	nC
Switching Characteristics						
t _{d(on)}	Turn-On Delay Time	V _{GS} = 4V, V _{DS} = 10V, R _G = 10Ω, I _D = 1A	-	18	-	ns
t _r	Turn-On Rise Time		-	5	-	ns
t _{d(off)}	Turn-Off Delay Time		-	43	-	ns
t _f	Turn-Off Fall Time		-	20	-	ns
Drain-Source Diode Characteristics and Maximum Ratings						
V _{SD}	Drain to Source Diode Forward Voltage	V _{GS} = 0V, I _{SD} = 1.7A			1.2	V

TYPICAL PERFORMANCE CHARACTERISTICS



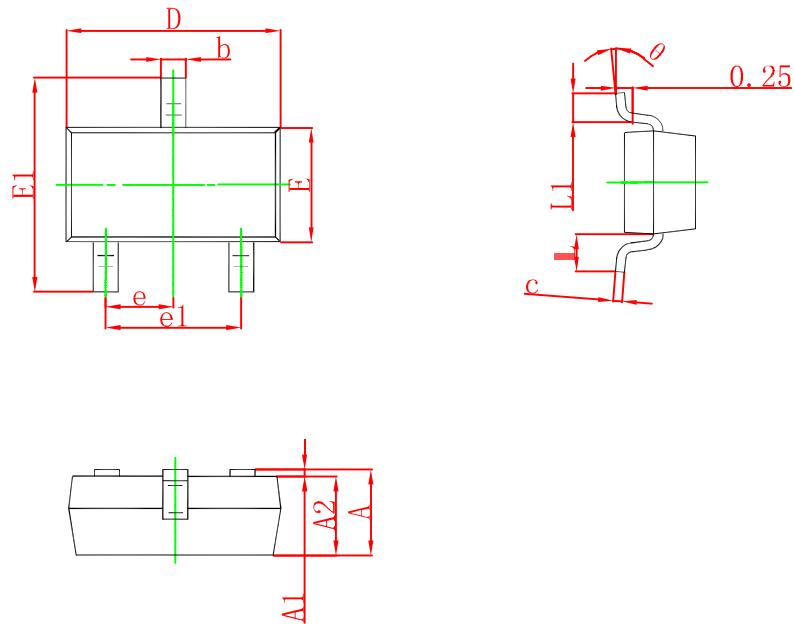


ZTSOC

江苏朝图微电子有限公司

ZT2300

SOT-23 PACKAGE OUTLINE DRAWING



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min	Max	Min	Max
A	0.900	1.150	0.035	0.045
A1	0.000	0.100	0.000	0.004
A2	0.900	1.050	0.035	0.041
b	0.300	0.500	0.012	0.020
c	0.080	0.150	0.003	0.006
D	2.800	3.000	0.110	0.118
E	1.200	1.400	0.047	0.055
E1	2.250	2.550	0.089	0.100
e	0.950 TYP		0.037 TYP	
e1	1.800	2.000	0.071	0.079
L	0.550 REF		0.022 REF	
L1	0.300	0.500	0.012	0.020
θ	0°	8°	0°	8°